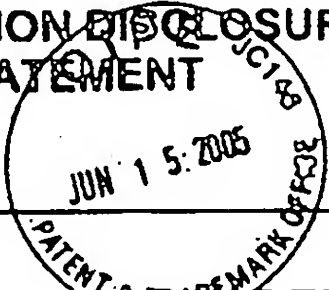
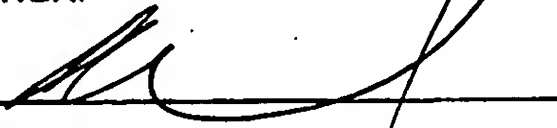



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	Serial No.:	NOT YET ASSIGNED
	Applicant:	MEARS
	Filing Date:	HEREWITH
	Group:	

U.S. PATENT DOCUMENTS							
Examiner Initials		Document Number	Date	Name	Class	Sub Class	Filing Date
	AA	4,594,603	06/10/86	Holonyak, Jr.	357	16	01/24/85
	AB	4,937,204	06/26/90	Ishibashi et al.	437	110	01/4/89
	AC	4,969,031	11/06/90	Kobayashi et al.	357	63	02/3/83
	AD	5,05,887	10/08/91	Yamazaki	357	4	01/18/90
	AE	5,218,262	06/1/93	Tsu	257	17	03/2/92
	AF	5,357,119	10/18/94	Wang et al.	257	18	02/19/93
	AG	5,684,817	11/04/97	Houdre et al.	372	45	05/1/96
	AH	5,683,934	11/4/03	Candelaria	437	134	05/3/96
	AI	5,994,164	11/30/99	Ponash et al.	438	97	03/18/98
	AJ	6,058,127	05/2/00	Joannepeoules et al.	372	92	12/12/97
	AK	6,274,007	08/14/01	Smirnov et al.	204	192	03/14/00
	AL	6,281,518	08/28/01	Sato	257	13	12/3/98
	AM	6,281,532	08/28/01	Doyle et al.	257	288	06/28/99
	AN	6,344,271	02/05/02	Yadav et al.	428	402	03/23/99
	AO	6,472,885	10/29/02	Takagi	257	77	12/2/98
	AP	6,498,359	12/24/02	Schmidt et al.	257	190	05/18/01
	AQ	2003/0034529	02/20/03	Fitzgerald et al.	257	369	10/8/02
	AR	2003/0057416	03/27/03	Currie et al.	257	19	09/20/02

FOREIGN PATENT DOCUMENTS							
		Document Number	Date	Country	Class	Sub Class	Translation
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	AT	2,347,520	09/06/00	GB	G02B	5/18	
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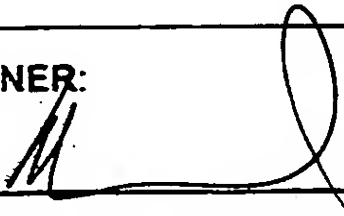
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	Group:	

OTHER ART (Including Author, Title, Date, Pertinent Pages, etc.)		
	AV	Xuan Luo et al.; "Chemical Design of Direct-Gap Light-Emitting Silicon", published July 25, 2002 by The American Physical Society, Vol. 89, Number 7
	AW	R. Tsu, University of North Carolina at Charlotte, "Phenomena in Silicon Nanostructure Devices"; published 09/05/2000 © Springer-Verlag 2000
	AX	P.D. Ye et al. "GaAs MOSFET with Oxide Gate Dielectric Grown by Atomic Layer Deposition"; © 2003 Agere Systems, March 2003
	AY	Novikov et al.; "Silicon-based Optoelectronics" © 1999-2003 by John Wiley & Sons, Inc.; pp/ 1-6
	AZ	
	BA	



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SUBSTITUTE FORM PTO-1449A LIST OF PATENTS AND APPLICANT'S INFORMATION DISCLOSURE STATEMENT	Atty Docket:	62603_CON2
	Serial No.:	10/717,370
	Applicant:	MEARS ET AL.
	Filing Date:	11/19/03
	Group:	1722


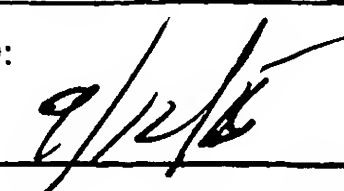
U.S. PATENT DOCUMENTS							
Examiner Initials		Document Number	Date	Name	Class	Sub Class	Filing Date
	AA	4,882,609	11/21/89	Schubert et al.	357	22	
	AB	5,081,513	1/14/92	Jackson et al.	357	23.7	
	AC	5,606,177	2/25/97	Wallace et al.	257	25	
	AD	6,255,150	7/3/01	Wilk et al.	438	191	
	AE	4,908,678	3/13/90	Yamazaki	357	4	
	AF						
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	AL						
FOREIGN PATENT DOCUMENTS							
		Document Number	Date	Country	Class	Sub Class	Translation
	AM	0 843 361	5/20/98	EP	H01L29	76	
	AN						
	AO						
	AP						
OTHER ART (Including Author, Title, Date, Pertinent Pages, etc.)							
	AQ	Patent Abstracts of Japan, Vol. 012, No. 080 (E-590), 12 March 1988 & JP 62 219665 A (Fujitsu Ltd), 26 September 1987 abstract					
	AR	Patent Abstracts of Japan, Vol. 010, No.179 (E-414), 24 June 1986 & JP 61 027681 A (Res Dev Corp of Japan), 7 February 1986 abstract					
	AS						

EXAMINER: 	DATE CONSIDERED: 9/8/05
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U.S. PATENT DOCUMENTS							
Examiner Initials		Document Number	Date	Name	Class	Sub Class	Filing Date
/	AA	4,594,603	06/10/86	Holonyak, Jr.	357	16	01/24/85
	AB	4,937,204	06/26/90	Ishibashi et al.	437	110	01/4/89
	AC	4,969,031	11/06/90	Kobayashi et al.	357	63	02/3/83
	AD	5,05,887	10/08/91	Yamazaki	357	4	01/18/90
	AE	5,216,262	06/1/93	Tsu	257	17	03/2/92
	AF	5,357,119	10/18/94	Wang et al.	257	18	02/19/93
	AG	5,684,817	11/04/97	Houdre et al.	372	45	05/1/96
	AH	5,683,934	11/4/03	Candelaria	437	134	05/3/96
	AI	5,994,164	11/30/99	Fonash et al.	438	97	03/18/98
	AJ	6,058,127	05/2/00	Joannopoulos et al.	372	92	12/12/97
	AK	6,274,007	08/14/01	Smirnov et al.	204	192	03/14/00
	AL	6,281,518	08/28/01	Sato	257	13	12/3/98
	AM	6,281,532	08/28/01	Doyle et al.	257	288	06/28/99
	AN	6,344,271	02/05/02	Yadav et al.	428	402	03/23/99
	AO	6,472,685	10/29/02	Takagi	257	77	12/2/98
	AP	6,498,359	12/24/02	Schmidt et al.	257	190	05/18/01
/	AQ	2003/ 0034529	02/20/03	Fitzgerald et al.	257	369	10/8/02
/	AR	2003/ 0057416	03/27/03	Currie et al.	257	19	09/20/02
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/	AS	02/103767	12/27/02	WO	H01L	21/20	
/	AT	2,347,520	09/06/00	GB	G02B	5/18	
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	AW	R. Tsu; University of North Carolina at Charlotte, "Phenomena in Silicon Nanostructure Devices"; published 09/06/2000 © Springer-Verlag 2000
	AX	P.D. Ye et al., "GaAs MOSFET with Oxide Gate Dielectric Grown by Atomic Layer Deposition"; © 2003 Agere Systems, March 2003
	AY	Novikov et al.; "Silicon-based Optoelectronics" © 1999-2003 by John Wiley & Sons, Inc.; pp/ 1-6
	AZ	
	BA	

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